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(71) Applicant *(for all designated States except US)*: **CANON KABUSHIKI KAISHA** [JP/JP]; 3-30-2, Shimomaruko, Ohta-ku, Tokyo 146-8501 (JP).

(72) Inventor; and

(75) Inventor/Applicant *(for US only)*: **UNNO, Akira** [JP/JP]; c/o CANON KABUSHIKI KAISHA, 3-30-2, Shimomaruko, Ohta-ku, Tokyo 146-8501 (JP).

(74) Agents: **OKABE, Masao** et al.; No. 602, Fuji Bldg., 2-3, Marunouchi 3-chome, Chiyoda-ku, Tokyo 100-0005 (JP).

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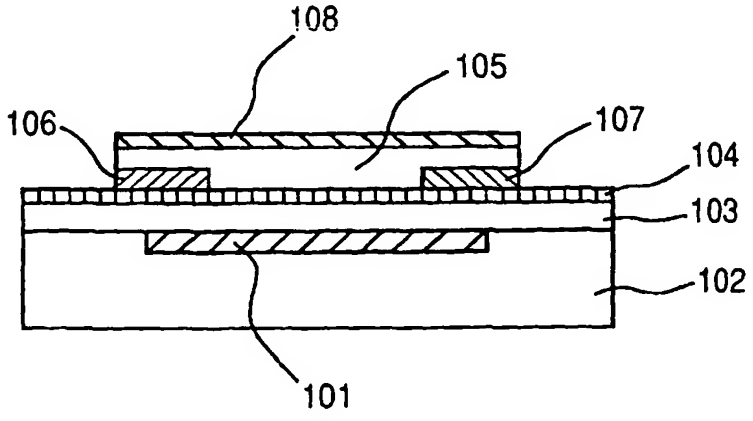
(54) Title: ORGANIC SEMICONDUCTOR ELEMENT, PRODUCTION METHOD THEREFOR AND ORGANIC SEMICONDUCTOR DEVICE



(57) Abstract: An organic semiconductor element is provided which has the controlled crystalline state of a vapor-deposited pentacene layer and a high mobility with low voltage driving. The organic semiconductor element is formed by providing a gate electrode 101 on the surface of a substrate 102, providing thereon a gate insulating layer 103, providing on the surface of the gate insulating layer 103 an island-shaped protrusion layer 104 having dispersed and island-shaped protrusions with a low surface energy, providing on the island-shaped protrusion layer 104 a source electrode 106 and a drain electrode 107 with a distance therebetween, providing thereon an organic semiconductor layer 105 in contact with the island-shaped protrusion layer 104 and both electrodes 106 and 107, and further providing a protective film 108 on the organic semiconductor layer 105.